## ABSTRACT OF THE DISCLOSURE

It is intended to provide a semiconductor memory device capable of making margin of readout operation constant regardless of any selected memory cells wherein the number of reference cells is restrained to minimum essential number and reference current value of which depends on a selected memory cell is obtained. A memory cell selected by address Y(X) is connected to a data line DB and data in the memory cell is read out from a memory cell array 3. Then, a differential amplifier 4 amplifies the data with reference to a reference value supplied to a reference line RB from a reference section 2. The reference section 2 is constituted by a reference cell RC and a source resistance adjustor section 1 that is connected to a source terminal of the reference cell RC. A load adjustor section 1 adjusts a resistance value that is connected to the source terminal of the reference cell RC by the address Y(X). A source resistance adjustor section 1 connects a load equivalent to a load selected by a memory cell in accordance with the address Y(X) to the reference cell RC, whereby an appropriate reference value is constantly supplied.